Nilanthy Balakrishnan

List of Publications by Year in descending order

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933447 940533 16 850 10 16 citations g-index h-index papers 16 16 16 1774 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Production and processing of graphene and related materials. 2D Materials, 2020, 7, 022001.	4.4	333
2	Tunable van Hove singularities and correlated states in twisted monolayer–bilayer graphene. Nature Physics, 2021, 17, 619-626.	16.7	103
3	Epitaxial growth of $\langle i \rangle \hat{I}^3 \langle i \rangle$ -lnSe and $\langle i \rangle \hat{I}^2 \langle i \rangle$, $\langle i \rangle \hat{I}^2 \langle i \rangle$, and $\langle i \rangle \hat{I}^3 \langle i \rangle$ -ln $\langle sub \rangle 2 \langle sub \rangle$ Se $\langle sub \rangle 3 \langle sub \rangle$ on $\langle i \rangle \hat{I}_\mu \langle i \rangle$ -GaSe. 2D Materials, 2018, 5, 035026.	4.4	98
4	Quantum confinement and photoresponsivity of $\langle i \rangle \hat{l}^2 \langle i \rangle$ -ln $\langle sub \rangle 2 \langle sub \rangle$ Se $\langle sub \rangle 3 \langle sub \rangle$ nanosheets grown by physical vapour transport. 2D Materials, 2016, 3, 025030.	4.4	88
5	Engineering <i>p</i> – <i>n</i> junctions and bandgap tuning of InSe nanolayers by controlled oxidation. 2D Materials, 2017, 4, 025043.	4.4	76
6	Room Temperature Electroluminescence from Mechanically Formed van der Waals III–VI Homojunctions and Heterojunctions. Advanced Optical Materials, 2014, 2, 1064-1069.	7.3	71
7	Band-gap profiling by laser writing of hydrogen-containing III-N-Vs. Physical Review B, 2012, 86, .	3.2	18
8	Ferroelectric semiconductor junctions based on graphene/In ₂ Se ₃ /graphene van der Waals heterostructures. 2D Materials, 2021, 8, 045020.	4.4	16
9	Anomalous Low Thermal Conductivity of Atomically Thin InSe Probed by Scanning Thermal Microscopy. Advanced Functional Materials, 2021, 31, 2008967.	14.9	15
10	Laser writing of the electronic activity of N- and H-atoms in GaAs. Applied Physics Letters, 2011, 99, 021105.	3.3	10
11	Memristive effects due to charge transfer in graphene gated through ferroelectric CulnP ₂ S ₆ . 2D Materials, 2022, 9, 035003.	4.4	10
12	A micrometer-size movable light emitting area in a resonant tunneling light emitting diode. Applied Physics Letters, 2013, 103, .	3.3	3
13	Synchrotron x-ray diffraction study of micro-patterns obtained by spatially selective hydrogenation of GaAsN. Applied Physics Letters, 2015, 106, 051905.	3.3	3
14	Optical Detection and Spatial Modulation of Midâ€Infrared Surface Plasmon Polaritons in a Highly Doped Semiconductor. Advanced Optical Materials, 2018, 6, 1700492.	7.3	3
15	Imaging shape and strain in nanoscale engineered semiconductors for photonics by coherent x-ray diffraction. Communications Materials, 2020, 1 , .	6.9	2
16	Tunable spectral response by hydrogen irradiation of Ga(AsN) superlattice diodes. Applied Physics Letters, 2014, 104, 242110.	3.3	1